

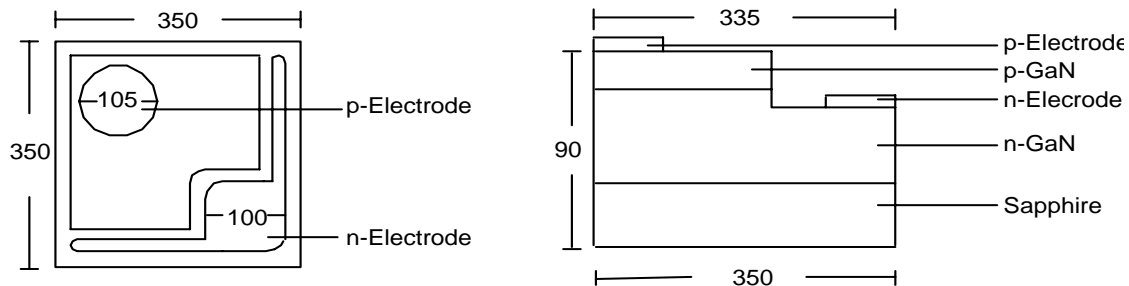
■ Features :

- MOVPE epi wafer
- Suitable for new creative products
- Excellent bondability

■ Typical Applications :

- Lamp
- Back Light
- Dot Matrix
- Display
- SMD chip LED
- Light Bar

■ Outline Dimensions : (Unit: um)



■ Physical Structure :

Chip dimension	Chip size	350um x 350um
	Thickness	90um
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold

■ Electro-Optical Characteristics : (Ta = 25 °C)

Parameter	Symbol	Condition	Grades	Min.	Typ.	Max.	Unit
Forward Voltage	V _f	I _{FDC} = 20 mA	A	-	-	3.4	Volts
Reverse Voltage	V _{br}	I _R = 10 μA		8.0	-	-	Volts
Dominant Wavelength	W _{ld}	I _{FDC} = 20 mA	15	515	-	520	nm
			20	520	-	525	
			25	525	-	530	
			30	530	-	535	
Intensity	I _v	I _{FDC} = 20 mA	1	-	75-100	-	mcd
			2	-	100-125	-	
			3	-	125-150	-	
			4	-	150-175	-	
			5	-	175-200	-	

For 20 mA sorting specification



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■ **Typical Electro-Optical Characteristics Curve:**

Fig 1. Forward Current vs. Forward Voltage

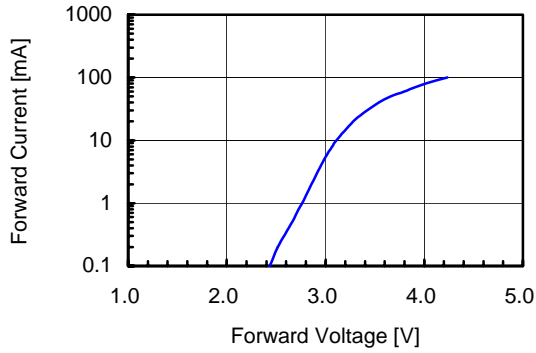


Fig 2. Relative Intensity vs. Forward Current

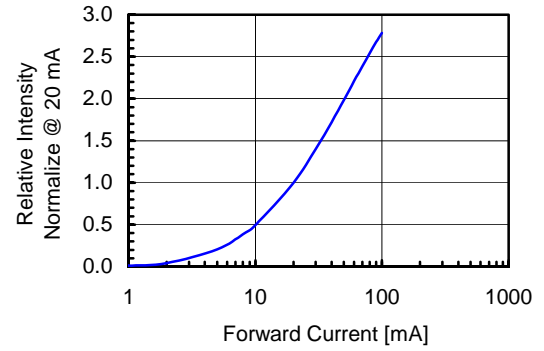


Fig 3. Forward Voltage vs. Temperature

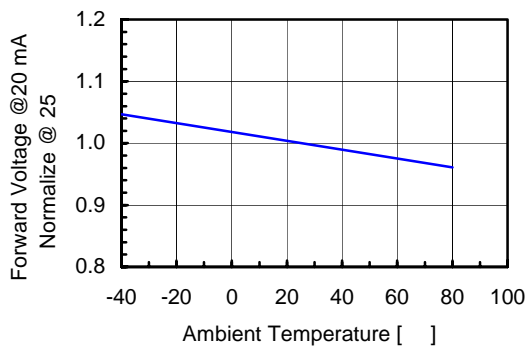


Fig 4. Relative Intensity vs. Temperature

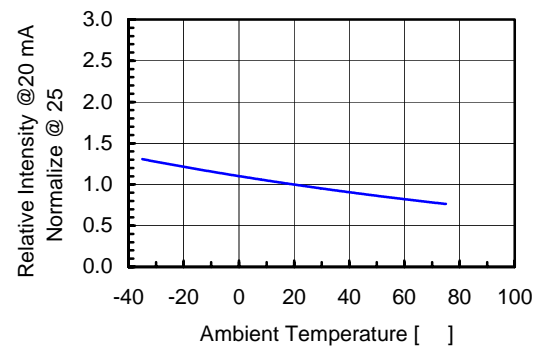


Fig 5. Relative Intensity vs. Wavelength

